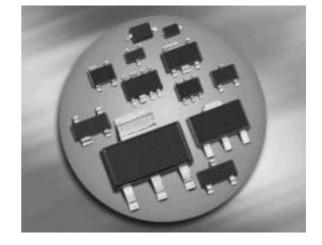


Silicon Switching Diode

- Electrically insulated high-voltage medium-speed diodes
- Pb-free (RoHS compliant) package 1)
- Qualified according AEC Q101





BAW101



Туре	Package	Configuration	Marking
BAW101	SOT143	parallel	JPs

Maximum Ratings at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V _R	300	V
Peak reverse voltage	V _{RM}	300	
Forward current	/ _F	250	mA
Peak forward current	/ _{FM}	500	
Peak forward current	I _{FM}	500	mA
Surge forward current, $t = 1 \mu s$	I _{FS}	4.5	А
Non-repetitive peak surge forward current	I _{FSM}	-	
Total power dissipation	P _{tot}	350	mW
<i>T</i> _S ≤ 35°C			
Junction temperature	T_{j}	150	°C
Storage temperature	T _{stg}	-65 150	

¹Pb-containing package may be available upon special request



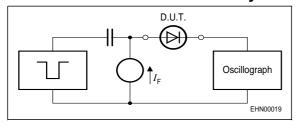
Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}	≤ 330	K/W
BAW101			

Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics		1			
Breakdown voltage	V _(BR)	300	-	-	V
$I_{(BR)} = 100 \mu A$					
Reverse current	I _R				μΑ
$V_{R} = 250 \text{ V}$		-	-	0.15	
$V_{R} = 250 \text{ V}, T_{A} = 150 ^{\circ}\text{C}$		-	-	50	
Forward voltage	V _F	-	-	1.3	V
$I_{\rm F} = 100 \text{mA}$					
AC Characteristics					
Diode capacitance	CT	-	6	-	pF
$V_{R} = 0 \text{ V}, f = 1 \text{ MHz}$					
Reverse recovery time	<i>t</i> _{rr}	-	1	-	μs
I_F = 10 mA, I_R = 10 mA, measured at I_R = 1mA,					
$R_{\rm L}$ = 100 Ω					

Test circuit for reverse recovery time



Pulse generator: $t_{\rm p}$ = 10 μ s, D = 0.05, $t_{\rm r}$ = 0.6ns, $R_{\rm i}$ = 50 Ω

Oscillograph: $R = 50\Omega$, $t_r = 0.35$ ns, $C \le 1$ pF

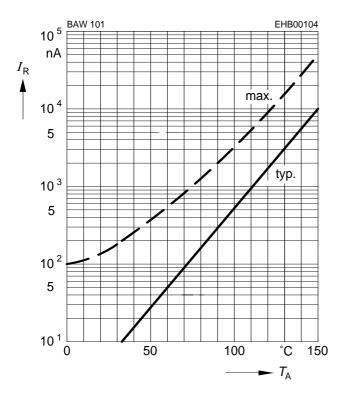
2

 $^{^{1}\}mathrm{For}$ calculation of R_{thJA} please refer to Application Note Thermal Resistance



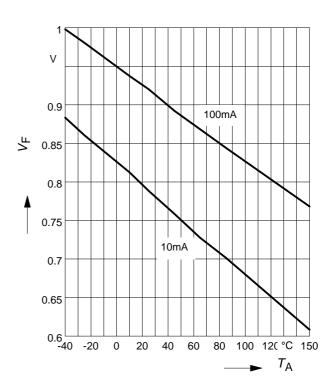
Reverse current $I_R = f(T_A)$

$$V_{R} = 250 V$$



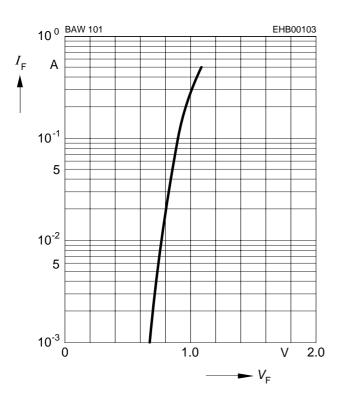
Forward Voltage $V_F = f(T_A)$

 I_{F} = Parameter



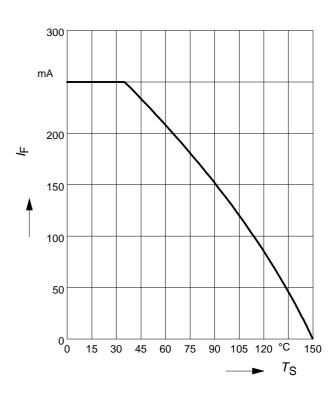
Forward current $I_F = f(V_F)$

$$T_A = 25^{\circ}C$$



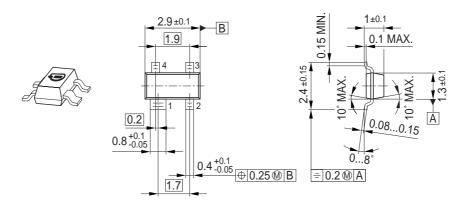
Forward current $I_F = f(T_S)$

BAW101

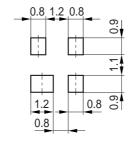




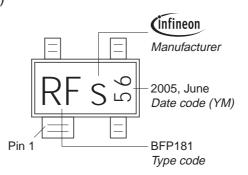
Package Outline



Foot Print

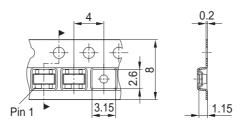


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel



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